



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/332,271
Confirmation No. None
Filing Date June 11, 1999
Inventor Klaus Florian Schuegraf et al.
Assignee Micron Technology, Inc.
Group Art Unit 2812
Examiner Ron E. Pompey
Attorney's Docket No. MI22-532
Customer No. 21567
Title: Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects,
and Wordline, Transistor Gate, and Conductive Interconnect Structures

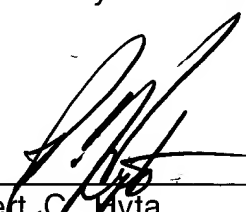
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. No admission is made regarding whether any of the submitted references is prior art. Copies of the references are attached.

Respectfully Submitted:

Dated: 8/28/03

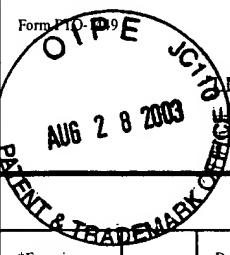

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Form PTO-09 		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-532		SERIAL NO. 09/332,271	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Klaus Florian Schuegraf et al.			
				FILING DATE June 11, 1999		GROUP 2812	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AN		Ohnishi, K. et al., <i>Improving Gate Oxide Integrity (GOI) of a W/Wnx/dual-poly Si Stacked-Gate by Using Wet-Hydrogen Oxidation in 0.14- μm CMOS devices</i> , IEDM, 1998, pgs. 397-400.				
	AO		Kawada, K. et al., <i>Water Vapor Generator By catalytic Reactor</i> , pgs. 10-16.				
	AP		Wakabayashi, H. et al., <i>An Ultra-Low Resistance and Thermo Stable W/pn-Poly-Si Gate CMOS Technology using Si/TiN Buffer Layer</i> , IEDM, 1998, pgs. 393-396.				
			Hiura, Y. et al., <i>Integration Technology of Polymetal (W/WSiN/Poly-Si) Dual Gate CMOS for 1 Gbit DRAMs and Beyond</i> , IEDM, 1998, pgs. 389-392.				
			Nagahama, T. et al., <i>Wet Hydrogen Oxidation System for Metal Gate LSI's</i> , pgs. 140-143				
			Lee, B. et al., <i>In-situ Barrier Formation for High Reliable W/barrier/poly-Si Gate Using Denudation of W_{ox} on Polycrystalline Si</i> , IEDM, 1998 pgs. 385-389.				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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